

GT04 Series Gate Drive Transformer



Features

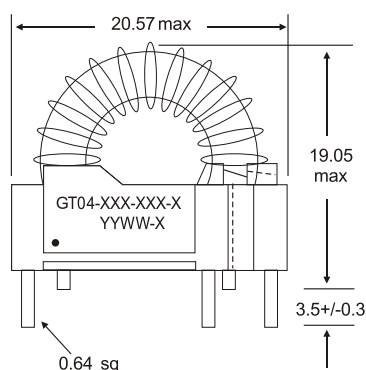
- ◆ Meets medical safety isolation requirements
- ◆ Designed for frequencies from 20 kHz to 300 kHz
- ◆ Available in UL Class F (155°C) or Economical Class B (130°C) Versions

Applications

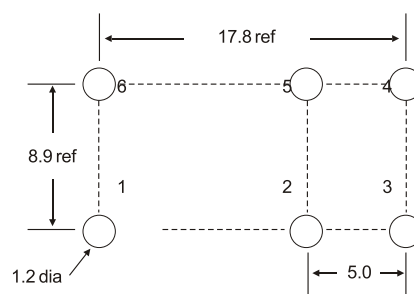
- ◆ Gate Drive Transformer
- ◆ Signal Transformer Across Isolation Barriers
- ◆ Off-Line AC/DC Converters
- ◆ High-Powered DC/DC Converters

Packaging Tray=45 pieces, Box=12 trays, Box=540 pieces

Mechanical

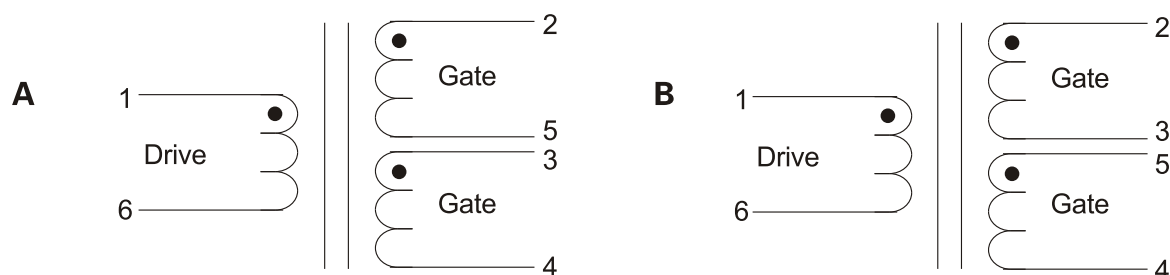


Recommended PCB Layout



Unit: mm

Schematic



Gate Drive Transformer

GT04 Series

ELECTRICAL SPECIFICATIONS — STANDARD VERSION

Part No ⁵	Turns Ratio (Drive : Gate)	Primary ¹ Inductance (mH min.)	DCR (Ω max.) N1:N2:N3	Leakage Inductance (μ H max.)	E-T Product ⁶ (V- μ s)	HiPot (V _{dc})
CT04-111-063	1:1:1	0.247	0.04:0.04:0.04	0.2	63	4500
CT04-111-126	1:1:1	0.990	0.07:0.07:0.07	0.4	126	4500
CT04-111-189	1:1:1	2.220	0.2:0.2:0.2	0.5	189	4500
CT04-111-252	1:1:1	3.960	0.5:0.5:0.5	.7	252	4500
CT04-111-315	1:1:1	6.180	1:1:1	.7	315	4500
CT04-111-378	1:1:1	8.810	2.7:2.7:2.7	1.2	378	4500
CT04-122-063	1: 2.5: 2.5	0.039	0.02:0.04:0.04	0.15	63	4500
CT04-122-126	1: 2.5: 2.5	0.158	0.04:0.07:0.07	0.2	126	4500
CT04-122-189	1: 2.5: 2.5	0.356	0.1:0.2:0.2	0.25	189	4500
CT04-122-252	1: 2.5: 2.5	0.634	0.2:0.45:0.45	0.3	315	4500
CT04-122-315	1: 2.5: 2.5	0.990	0.4:0.9:0.9	0.4	315	4500
CT04-122-378	1: 2.5: 2.5	1.420	1.1:2.5:2.5	0.5	378	4500

ELECTRICAL SPECIFICATIONS — ECONOMY VERSION

Part No ⁵	Turns Ratio (Drive : Gate)	Primary ¹ Inductance (mH min.)	DCR (Ω max.) N1:N2:N3	Leakage Inductance (μ H max.)	E-T Product ⁶ (V- μ s)	HiPot (V _{dc})
CT04-111-063_E	1:1:1	0.247	0.07:0.04:0.04	0.4	63	4500
CT04-111-126_E	1:1:1	0.990	0.16:0.07:0.07	0.6	126	4500
CT04-111-189_E	1:1:1	2.220	0.2:0.2:0.2	0.5	189	4500
CT04-111-252_E	1:1:1	3.960	0.8:0.5:0.5	0.9	252	4500
CT04-111-315_E	1:1:1	6.180	1:1:1	0.8	315	4500
CT04-111-378_E	1:1:1	8.910	1.2:2.7:2.7	1.5	378	4500
CT04-122-063_E	1: 2.5: 2.5	0.039	0.04:0.04:0.04	0.4	63	4500
CT04-122-126_E	1: 2.5: 2.5	0.158	0.06:0.07:0.07	0.4	126	4500
CT04-122-189_E	1: 2.5: 2.5	0.356	0.1:0.2:0.2	0.25	189	4500
CT04-122-252_E	1: 2.5: 2.5	0.634	0.34:0.45:0.45	0.6	252	4500
CT04-122-315_E	1: 2.5: 2.5	0.990	0.4:0.9:0.9	0.4	315	4500
CT04-122-378_E	1: 2.5: 2.5	1.420	0.5:2.5:2.5	0.9	378	4500

1. Tested at 10 kHz, 0.1Vrms
2. Electrical specifications at 25°C.
3. Operating range: -40°C to +130°C.
4. Meets UL 84V-0.
5. Select pin assignment option based on schematics above. For other options please contact
Select pin assignment option based on schematics For other options please contact
6. E-T product rating is for the secondary (gate) windings and is based upon a peak flux density of
2200 Gauss at 25°C when used in a bipolar -driven application.



SHAANXI SHINHOM ENTERPRISE CO.,LTD

PULSE GATE DRIVE TRANSFORMER

These transformers are wound on high quality ferrite core and are intended for a very wide range of applications:

- firing thyristors and triacs;
- driving bipolar transistor and IGBT;
- driving FET and MOSFET transistors;
- line coupling in high speed data transmission (for the smallest sizes).

Three case sizes are presented, with increasing power rating, so that they can effectively find use as drivers in any low-to-medium power circuit for control and conversion of electrical energy, where the following features are requested at the same time:

- high power pulse trasmission capability (high amplitude with proper duration) and low magnetization current;
- low leakage inductance, wich allows high steepness and short rise time of the wave form;
- low coupling capacitance, so that a good decoupling and immunity to interferences is reached;
- small size, achivied with the use of toroidal core;
- high primary to secondary withstanding voltage by means of a proper wires insulation and rosin filling;
- international standards compliance.



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PULSE GATE DRIVE TRANSFORMER

Symbol Definitions

Turns Ratio (n)

Turns ratio of the primary winding to each secondary winding; first digit refers to the primary.

Voltage-time Area (U•t)

Minimum Voltage-time product of the pulse amplitude and pulse width, measured at half of the pulse height across the unloaded secondary in the unipolar mode.

Primary Inductance (PRI Induct)

Inductance of the primary winding measured at 10 kHz/0,1 mA (reference values only)

Primary Leakage Inductance (PRI Leak Induct)

Leakage inductance of the primary winding with secondary winding(s) connected in series and short circuited; measured at 100 kHz.

Winding Capacitance (PRI/SEC Cw/w)

Coupling capacitance between primary and secondary winding(s); measured at 10 kHz.

Primary Resistance (PRI DCR)

DC resistance of the primary winding.

Secondary Resistance (SEC DCR)

DC resistance of (each) secondary winding.

Test Voltage (Up)

Unrepeated test voltage at 50 Hz/1 to 2 sec, between primary to secondary winding(s).

Ignition Current (I c)

Reference current value giving a low voltage - drop under 1 V - across the secondary resistance.

Pulse Rise Time (Tr)

Rise time between 10% and 90% of the output pulse amplitude, measured on the secondary loaded with RL resistor.

Secondary resistor load (RL)

Working Voltage (Ueff)

Maximum rms working voltage of primary winding.

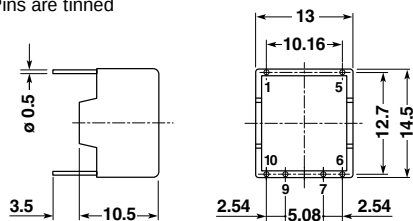
CASE VERSION

Ignition current up to 100 mA

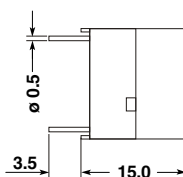
These small size and low power transformers are fitted on toroid cores of high performance (ferrite). The wide choice of inductance values and turn ratios make them suitable as drivers of thyristors, triacs, bipolar transistors or MOSFET's in a variety of high frequency applications, such as small power supplies, inverters etc., or also as couplers in high speed data transmission.

Dimensions in mm

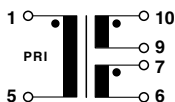
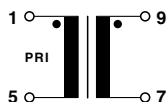
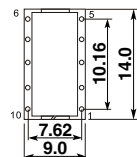
Pins are tinned



H: horizontal



V: vertical



- Pins
- Start of winding

TYPES

Code	Turns ratio n ± 2%	U • t Vµsec min.	Tr µsec max	PRI Indut mH	PRI Leak Induc µH	PRI/SEC Cw/w pF	PRI DCR Ω	SEC DCR Ω	Ueff V	Up kV
GT12V/H-101	1:1	65	0.05	1.0	1.5	35	0.20	0.20	250	2
GT12V/H-102	2:1	50	0.05	2.0	3.0	30	0.30	0.15	250	2
GT12V/H-103	1:1:1	45	0.05	0.5	0.8	24	0.15	0.15	250	2
GT12V/H-104	1:1	40	0.05	0.15	0.7	24	0.07	0.07	600	4
GT12V/H-105	1:1	45	0.05	0.5	0.7	30	0.08	0.08	600	4

Turns ratio: first digit refers to the primary.

Tr is measured with $R_L = 100 \Omega$

Other type can be supplied according to customer's specifications.

Symbol definitions p. 2

Technical Data

Climatic category:

DIN GKC (-40 to +125°C; humidity cat. C)

Overtemperature of the windings:

<55°C

Max. windings temperature:

115°C

Approx. weight:

3 g

The transformers are designed and tested in accordance with EN 138100; EN 60938-1

The cases are of flame-retardant plastic material in accordance with UL 94V-0



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PULSE GATE DRIVE TRANSFORMER

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- firing thyristors and triacs;
- driving bipolar transistor and IGBT;
- driving FET and MOSFET transistors;
- line coupling in high speed data transmission (for the smallest sizes).

Three case sizes are presented, with increasing power rating, so that they can effectively find use as drivers in any low-to-medium power circuit for control and conversion of electrical energy, where the following features are requested at the same time:

- high power pulse trasmission capability (high amplitude with proper duration) and low magnetization current;
- low leakage inductance, wich allows high steepness and short rise time of the wave form;
- low coupling capacitance, so that a good decoupling and immunity to interferences is reached;
- small size, achivied with the use of toroidal core;
- high primary to secondary withstanding voltage by means of a proper wires insulation and rosin filling;
- international standards compliance.



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Symbol Definitions

Turns Ratio (n)

Turns ratio of the primary winding to each secondary winding; first digit refers to the primary.

Voltage-time Area (U•t)

Minimum Voltage-time product of the pulse amplitude and pulse width, measured at half of the pulse height across the unloaded secondary in the unipolar mode.

Primary Inductance (PRI Induct)

Inductance of the primary winding measured at 10 kHz/0,1 mA (reference values only)

Primary Leakage Inductance (PRI Leak Induct)

Leakage inductance of the primary winding with secondary winding(s) connected in series and short circuited; measured at 100 kHz.

Winding Capacitance (PRI/SEC Cw/w)

Coupling capacitance between primary and secondary winding(s); measured at 10 kHz.

Primary Resistance (PRI DCR)

DC resistance of the primary winding.

Secondary Resistance (SEC DCR)

DC resistance of (each) secondary winding.

Test Voltage (Up)

Unrepeated test voltage at 50 Hz/1 to 2 sec, between primary to secondary winding(s).

Ignition Current (I c)

Reference current value giving a low voltage - drop under 1 V - across the secondary resistance.

Pulse Rise Time (Tr)

Rise time between 10% and 90% of the output pulse amplitude, measured on the secondary loaded with RL resistor.

Secondary resistor load (RL)

Working Voltage (Ueff)

Maximum rms working voltage of primary winding.



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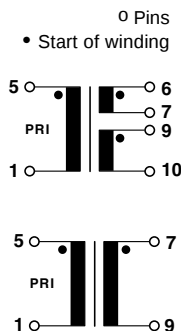
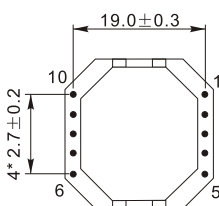
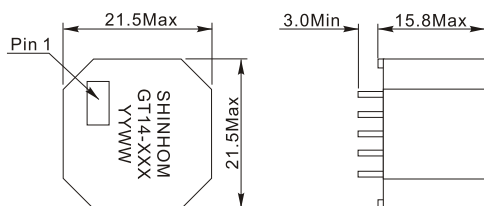
PULSE GATE DRIVE TRANSFORMER

CASE VERSION

Ignition up to 0.5 A

These small size and low power transformers are fitted on toroid cores of high performance (ferrite). The wide choice of inductance values and turn ratios make them suitable as drivers of thyristors, triacs, bipolar transistors or MOSFET's in a variety of high frequency applications, such as small power supplies, inverters etc.

Dimensions in mm



TYPES

Code	Turns ratio n ±2%	U • t Vµsec min.	Tr µsec max	PRI Indut mH	PRI Leak Induc µH	PRI/SEC Cw/w pF	PRI DCR Ω	SEC DCR Ω	Ueff V	Up kV
GT14-101	3:1	150	1	17	230	7	1.10	0.40	600	4
GT14-102	1:1	150	1.5	2	30	9	0.37	0.37	600	4
GT14-103	1:1	230	0.05	5	1	110	0.55	0.55	250	2
GT14-104	2:1	110	0.05	5	4	50	0.55	0.30	250	2
GT14-105	3:1	150	0.1	17	14	75	1.10	0.40	250	2
GT14-106	1:1:1	150	0.05	2	0.6	70	0.37	0.37	250	2
GT14-107	2:1:1	110	0.1	5	6	55	0.55	0.30	250	2
GT14-108	1:1	110	0.05	1	1	45	0.15	0.15	600	4
GT14-109	1:1	150	0.05	2	1	80	0.20	0.20	600	4
GT14-110	1:1:1	110	0.05	1	0.8	60	0.15	0.15	600	4

Turns ratio: first digit refers to the primary.
Tr is measured with RL = 47 Ω

Symbol definitions p. 2

Technical Data

Climatic category:

DIN GKC (-40 to +125°C; humidity cat. C)

Overtemperature of the windings:

<55°C

Max. windings temperature:

115°C

Approx. weight:

5 g

The transformers are designed and tested in accordance with EN 138100; EN 60938-1
The cases are of flame-retardant plastic material in accordance with UL 94V-0

GATE DRIVER TRANSFORMER

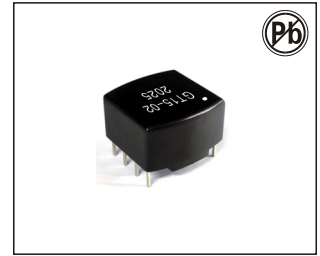
GT15 SERIES

FEATURES:

- RoHS compliant
- Inductance to 16.3mH
- Up to 482 V μ s Et rating
- PCB mounting
- UL94V-0 package materials
- Up to 4000Vrms isolation
- Backward compatible with Sn/Pb soldering systems

APPLCATIONS:

The GT15 series of pulse transformers are intended for medium power applications in switch mode power supplies and thyristor / triac firing (e.g. motor control applications). The standard turns ratios may be modified on any transformer with three windings by connecting any two windings in series.

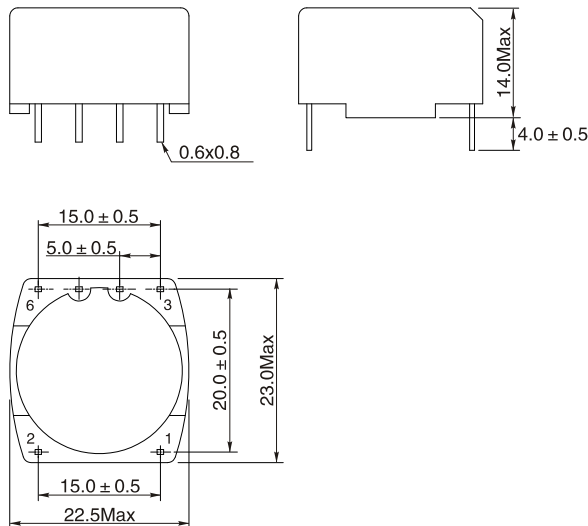


ELECTRICAL CHARACTERISTICS@25°C

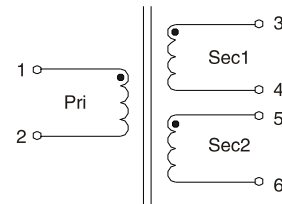
Part Number	Turns ratio	Pri Inductance (mH) Min 1.0KHz, 0.1V	Pri Et Constant (Vus) Min	LK (uH) Max 100KHz, 0.1V	Interwinding Capacitance (pF) Max	DCR			Hi-Pot (kVrms) 50Hz, 1S
						Pri (Ω) Max	Sec1 (Ω) Max	Sec2 (Ω) Max	
GT15-02	1:1:1	1.0	120	3.0	40	0.25	0.22	0.28	2.5
GT15-03	2:1:1	1.0	120	3.5	30	0.24	0.12	0.15	4.0
GT15-04	1:1	4.0	240	5.0	55	0.86	0.83	/	2.5
GT15-05	1:1:1	4.0	240	11.0	35	0.90	0.76	1.10	2.5
GT15-08	1:1:1	16.3	482	40.0	40	3.60	3.10	4.20	2.5
GT15-09	2:1:1	16.3	482	40.0	40	3.50	1.60	2.00	2.5

TECHNICAL INFORMATION & WINDING

Dimensions(mm)



Winding



ABSOLUTE MAXIMUM RATINGS

Operating temperature rang: 0°C to +70°C
Storage temperature rang: -60°C to +125°C

NOTES

Electrical specification at 25°C



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- low coupling capacitance, so that a good decoupling and immunity to interferences is reached;
- small size, achivied with the use of toroidal core;
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- international standards compliance.



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PULSE GATE DRIVE TRANSFORMER

Symbol Definitions

Turns Ratio (n)

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Primary Inductance (PRI Induct)

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Winding Capacitance (PRI/SEC Cw/w)

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Primary Resistance (PRI DCR)

DC resistance of the primary winding.

Secondary Resistance (SEC DCR)

DC resistance of (each) secondary winding.

Test Voltage (Up)

Unrepeated test voltage at 50 Hz/1 to 2 sec, between primary to secondary winding(s).

Ignition Current (I c)

Reference current value giving a low voltage - drop under 1 V - across the secondary resistance.

Pulse Rise Time (Tr)

Rise time between 10% and 90% of the output pulse amplitude, measured on the secondary loaded with RL resistor.

Secondary resistor load (RL)

Working Voltage (Ueff)

Maximum rms working voltage of primary winding.



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PULSE GATE DRIVE TRANSFORMER

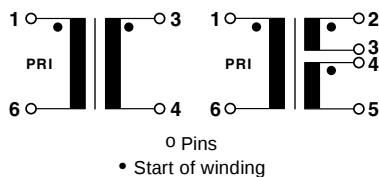
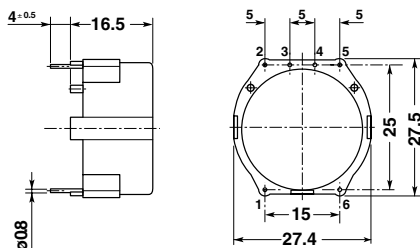
CASE VERSION

Ignition Current up to 1 A

These small size and low power transformers are fitted on toroid cores of high performance (ferrite). The wide choice of inductance values and turn ratios make them suitable as drivers of thyristors, triacs, bipolar transistors or MOSFET's in a variety of high frequency applications, such as small power supplies, inverters etc.

Dimensions in mm

Pins are tinned



TYPES

Code	Turns ratio n ±2%	U.t Vµsec min.	Tr µsec max	PRI Indut mH	PRI Leak Induc µH	PRI/SEC Cw/w pF	PRI DCR Ω	SEC DCR Ω	Ueff V	Up kV
GT16-101	1:1	230	4	2	25	12	0.37	0.37	600	4
GT16-102	1:1	180	0.2	1	1.0	40	0.15	0.15	600	4
GT16-103	1:1	280	0.3	2	1.8	60	0.20	0.20	600	4
GT16-104	1:1	450	0.4	5	2.0	125	0.33	0.33	600	4
GT16-105	1:1:1	180	0.2	1	1.0	45	0.15	0.15	600	4
GT16-106	2:1:1	120	0.2	2	2.0	40	0.20	0.10	600	4
GT16-107	2:1:1	220	0.2	5	3.5	80	0.35	0.16	600	4

Turns ratio: first digit refers to the primary.

Tr is measured with RL = 10 Ω

Symbol definitions p. 2

Other type can be supplied according to customer's specifications.

Technical Data

Climatic category:

DIN GKC (-40 to +125°C)

Overttemperature of the windings:

<55°C

Max. windings temperature:

115°C

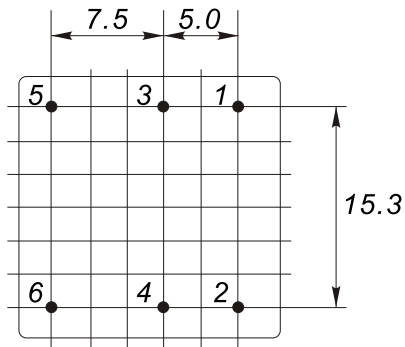
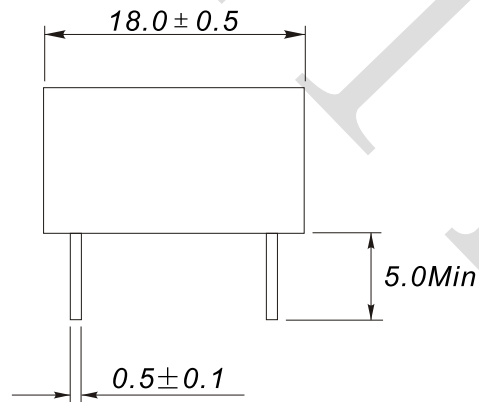
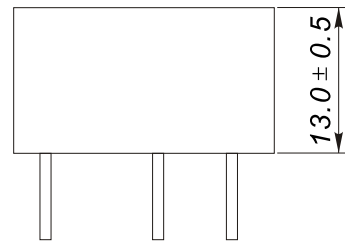
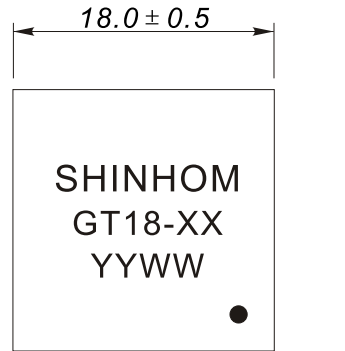
Approx. weight:

16 g

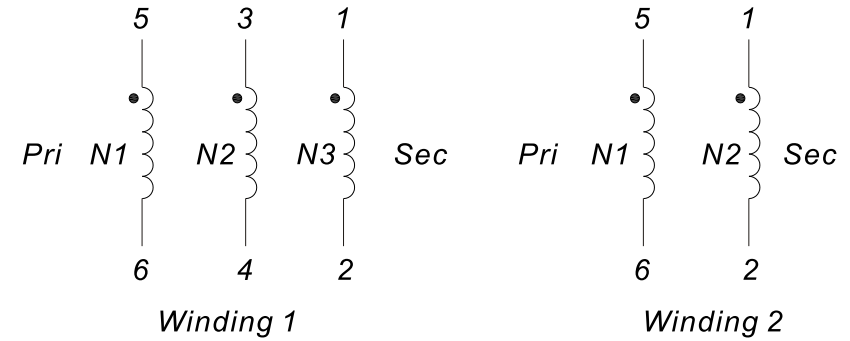
The transformers are designed and tested in accordance with EN 138100; EN 60938-1

The cases are of flame-retardant plastic material in accordance with UL 94V-0

1. PHYSICAL CHARACTERISTICS(mm)



2. ELECTRONICAL SCHEMATIC



3. ELECTRONICAL SPECIFICATIONS

Prat No. GT18-XXX	102	202	302	402	502	602	702	802	902	103	203
Turns ratio	1:1	1:1:1	1:1:1	2:1	2:1:1	3:1:1	1:1	2:1:1	3:1	2:1	1:1
Nominal voltage(V)	750	500	500	750	500	500	750	500	500	750	750
Voltage time area(Vus)	500	250	250	200	200	200	250	200	600	350	250
Pri Inductance(mH)	8	2.5	2.5	7	20	15	2.5	7	12	17	2.2
Leakage Inductance(uH)	100	75	85	35	100	70	3	55	30	80	40
DCR Pri(Ω)	1.4	0.6	0.7	1.8	5.6	2.8	0.62	1.8	1.8	3.2	0.8
Sec(Ω)	1.4	0.6	0.7	1	2.2	0.9	0.75	1	0.7	1.6	0.8
Coupling capacitance(pF)	10	7	7	7	7	9	80	7	8	7	8
Hi-Pot(KV)	4	3.2	3.2	4	4	4	4	3.2	3.2	3.2	4
Winding	2	1	1	2	1	1	2	1	2	2	2

NAME:	Pulse Gate drive Transformer		
CUSTOMER P/N:		DATE:	2011-09-07
SHINHOM P/N:	GT18 Series	REV: A0	PAGE
DRAWN BY	CHECKED BY	APPROVE BY	



SHINHOM
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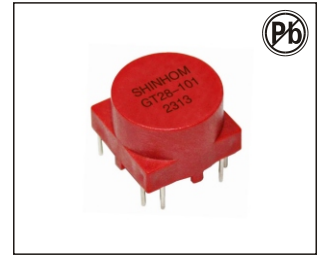
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GATE DRIVER TRANSFORMER FOR IGBT

GT28 SERIES

FEATURES:

- Low coupling capacitance, high anti-interference capability
- Low leakage, excellent output pulse waveform
- No switch delay, high instantaneous transmission power
- High electrical strength, safe and reliable
- Fully enclosed, good mechanical and corrosion resistance
- Compact size, DIP installation
- Size 30.14x27.94x25mm
- Conforms to UL91-V0

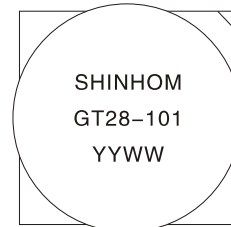
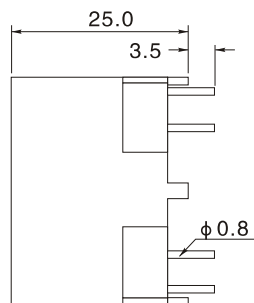
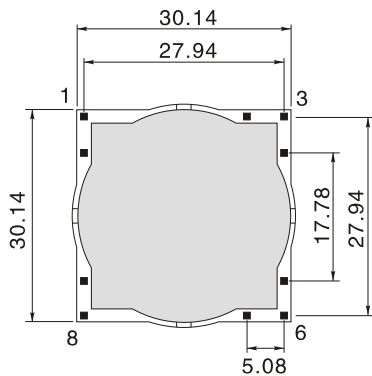


ELECTRICAL CHARACTERISTICS@25°C

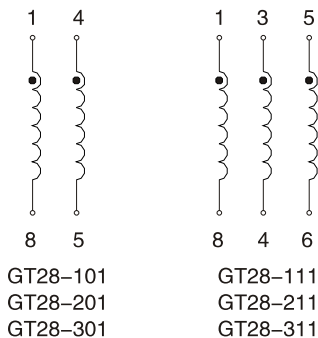
Part Number	Turns ratio	Pri Inductance (mH) 1.0KHz,0.3V	Pri impulse voltage (V)	Sec impulse voltage (V)	Pulse width (uS)	Et Constant (Vus) Min	Hi-Pot (kVrms) 50Hz,1min
GT28-101	1:1	2~5	15	13	66.6	1000	6
GT28-201	2:1	2~5	20	9	50	1000	6
GT28-301	3:1	2~5	30	9	33.3	1000	6
GT28-111	1:1:1	2~5	15	13	66.6	1000	6
GT28-211	2:1:1	2~5	20	9	50	1000	6
GT28-311	3:1:1	2~5	30	9	33.3	1000	6

TECHNICAL INFORMATION & WINDING

Dimensions(mm)



Winding



NOTES

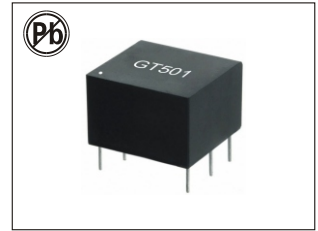
- Electrical specification at 25°C
- Ambient temperature ranges from -40°C to +85°C
- Insulation heat resistance Class F(155°C)
- Insulation resistance 1000MΩ Min
- Operating frequency 100Hz~50KHz

MOSFET / TRIAC / SCR Trigger transformers

GT SERIES

FEATURES:

- Ideal for use as trigger transformers in MOSFET,SCR and TRIACcircuits
- High isolation voltages – Hi-pot tested to 2500 VAC
- Fully encapsulated
- Designed for fast rise time applications

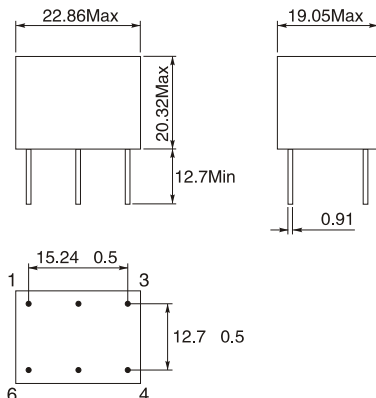


ELECTRICAL CHARACTERISTICS:@25°C

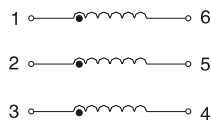
PART NUMBER	TURNS RATIO	PRIMARY INDUCTANCE (mH-MIN.)	PRIMARY ET-CONSTANT	LEAKAGE INDUCTANCE	Ciw (pf MAX.)	DCR PRI.	DCR SEC.	DCR SEC.	SCHEMATIC
GT500	1:1	0.25	45	5	20	1.0	1.0	N/A	2
GT501	1:1	1.0	90	20	30	2.0	2.0	N/A	2
GT502	1:1	5.0	180	45	30	3.0	3.0	N/A	2
GT503	1:1	20.0	360	200	50	5.0	5.0	N/A	2
GT504	1:1:1	0.25	45	5	20	1.0	1.0	1.0	1
GT505	1:1:1	1.0	90	20	30	2.0	2.0	2.0	1
GT506	1:1:1	5.0	180	45	30	3.0	3.0	3.0	1
GT507	1:1:1	20.0	360	200	50	5.0	5.0	5.0	1
GT508	2:1	1.0	90	40	30	2.0	1.0	N/A	2
GT509	2:1	5.0	180	60	30	3.0	2.0	N/A	2
GT510	2:1:1	1.0	90	40	30	2.0	1.0	1.0	1
GT511	2:1:1	5.0	180	60	30	3.0	2.0	2.0	1
GT512	5:1	20:0	360	200	50	5.0	2.0	N/A	2
GT513	5:1:1	20:0	360	200	50	5.0	2.0	2.0	1
GT570	1:1	0.25	45	5	20	1.0	1.0	N/A	3
GT571	1:1:1	0.25	45	5	20	1:0	1:0	1:0	4
GT572	1:1	1:0	90	20	30	2:0	2:0	N/A	3
GT573	1:1:1	1.0	90	20	30	2.0	2.0	2.0	4
GT574	1:1	5.0	180	45	30	3:0	3:0	N/A	3
GT575	1:1:1	5.0	180	45	30	3.0	3.0	3.0	4
GT576	1:1	20.0	360	200	50	6.0	6.0	N/A	3
GT577	1:1:1	20.0	360	75	50	3.0	3.0	3.0	4
GT578	2:1	1:0	90	40	30	2.0	1.0	N/A	3
GT579	2:1:1	1.0	90	60	30	2.0	1.0	1.0	4
GT580	2:1	5.0	180	40	30	3.0	2.0	N/A	3
GT581	2:1:1	5.0	180	45	30	3.0	2.0	2.0	4
GT582	2:1	20:0	360	200	75	5.0	3.0	N/A	3
GT583	2:1:1	20:0	360	200	75	3.0	2.0	2.0	4
GT584	5:1	20:0	360	200	50	5.0	2.0	N/A	3
GT585	5:1:1	20:0	360	200	50	5.0	2.0	2.0	4

MECHANICALS & SCHEMATICS

Dimensions(mm)



SCHEMATIC 1



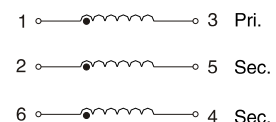
SCHEMATIC 3



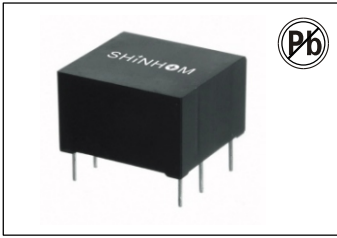
SCHEMATIC 2



SCHEMATIC 4



Note:All specifications subject to change without notice.



GATE DRIVE PULSE TRANSFORMERS

TX12XX SERIES

FEATURES:

- ROHS compliant
- UL94V-0 Package Material
- Isolation to 4Kvrms
- Compact Footprint
- PCB Mounting
- Backward compatible with Sn/PB Soldering systems.

OPTIONS:

- Bulk packaging is standard
- Custom design available

COMMON APPLICATIONS:

- Signal isolatin and use in small isolated power supplies.
- Gate drive circuit
- Power supplies
- Frequency converters
- Switching applicatins
- DC/DC converters
- Line coupling transformers in high-speed data transmission

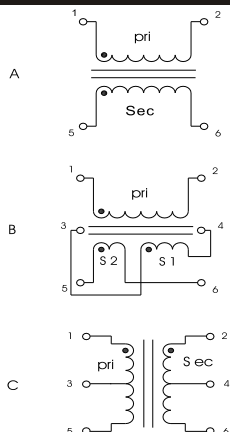
ELECTRICAL CHARACTERISTICS

Part NO	Turns Ratio ±2%	Min.Primary Inductance (MH)	Min.Primary constant,Er (Vus)	MinLeakage Indctance (Uh)	Max. Interwinding capacitance (PF)	Max.DC Resistance Primary Winding (Ω)	Max.DC Resistance Secondary 1 Winding (Ω)	Max.DC Resistance Secondary 2 Winding (Ω)	Isolation Voltage (Vrms)	Pin Connection Style	Mechanical Dimensions
TX1201	1:1	3.0	200	22	23	1.2	1.0	-	2000	A	2
TX1202	1:1:1	3.0	200	9	28	1.4	1.3	1.7	2000	B	1
TX1203	2:1:1	12	400	35	30	4.0	1.8	2.4	2000	B	1
TX1204	1:1:1	7.4	310	20	55	2.9	2.5	3.4	2000	B	1
TX1205	1:1:1	22	550	85	18	10.6	8.9	12.2	2000	B	1
TX1206	1:1:1	3.0	200	3	280	1.3	1.3	1.3	500VDC	B	1
TX1207	1:1	3.0	200	22	23	1.2	1.0	-	3500	A	2
TX1208	1:1	0.8	130	4	20	0.4	0.3	-	4000	A	2
TX1209	1.2CT: 1CT	8.8	340	60	25	2.5	2.5	-	2000	C	1
TX1210	2:1:1	24	570	70	20	7.5	3.5	4.5	2000	B	1
TX1211	1:1:1	6.0	285	30	30	4.0	4.0	4.0	2000	B	1
TX1212	100:1	6.1	280	-	6	0.7	0.1	-	2000	A	2

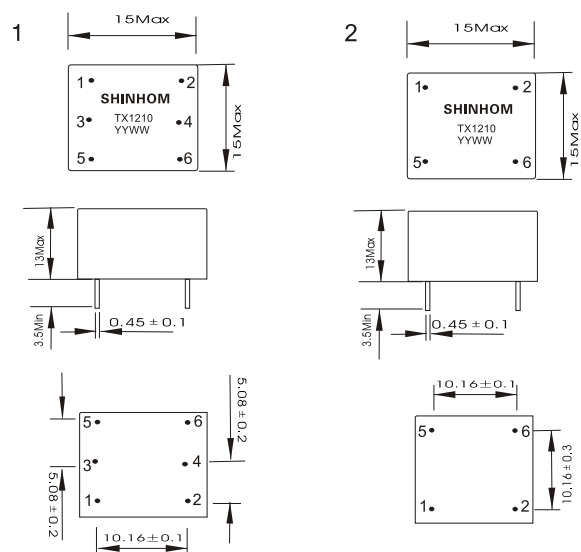
TECHNICAL INFORMATION

- Soldering methods : Wave, Reflow.
- Operating Temperature:0°C to 70°C.
- Storage Temperature : -55°C to 125°C.
- Peak wave solder temperature 300°C for 10 seconds.

PIN CONNECTIONS(TOP VIEW)



MECHANICAL DIMENSIONS



Note: All dimensions in mm